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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	40MHz
Connectivity	I ² C, SPI, UART/USART
Peripherals	LVD, PWM, WDT
Number of I/O	28
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 16x12b; D/A 2x6b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount, Wettable Flank
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-HVQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mke02z32vfm4r

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

- Timers
 - One 6-channel FlexTimer/PWM (FTM)
 - Two 2-channel FlexTimer/PWM (FTM)
 - One 2-channel periodic interrupt timer (PIT)
 - One real-time clock (RTC)
- Communication interfaces
 - Two SPI modules (SPI)
 - Up to three UART modules (UART)
 - One I2C module (I2C)
- Package options
 - 64-pin QFP/LQFP
 - 44-pin LQFP
 - 32-pin LQFP
 - 32-pin QFN

4.4 Voltage and current operating ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in the following table may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this document.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pullup resistor associated with the pin is enabled.

Symbol	Description	Min.	Max.	Unit
V _{DD}	Digital supply voltage	-0.3	6.0	V
I _{DD}	Maximum current into V _{DD}	—	120	mA
V _{IN}	Input voltage except true open drain pins	-0.3	V _{DD} + 0.3 ¹	V
	Input voltage of true open drain pins	-0.3	6	V
Ι _D	I _D Instantaneous maximum current single pin limit (applies to all port pins)		25	mA
V _{DDA}	Analog supply voltage	V _{DD} – 0.3	V _{DD} + 0.3	V

 Table 2.
 Voltage and current operating ratings

1. Maximum rating of V_{DD} also applies to $V_{\text{IN}}.$

5 General

5.1 Nonswitching electrical specifications

5.1.1 DC characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Γ	Symbol	С	Descriptions		Min	Typical ¹	Max	Unit
		_	Operating voltage	_	2.7	_	5.5	V

Table continues on the next page ...

Symbol	С		Descriptions			Typical ¹	Max	Uni
V _{OH}	Р	Output	All I/O pins, except PTA2	5 V, I _{load} = -5 mA	V _{DD} – 0.8	_		V
	С	high voltage	and PTA3, standard- drive strength	3 V, $I_{load} = -2.5 \text{ mA}$	$V_{DD} - 0.8$	—	—	V
	Р		High current drive pins,	5 V, $I_{load} = -20 \text{ mA}$	$V_{DD} - 0.8$	—	—	V
	С		high-drive strength ²	$3 \text{ V}, \text{ I}_{\text{load}} = -10 \text{ mA}$	V _{DD} – 0.8	—	—	V
I _{OHT}	D	Output	Max total I _{OH} for all ports	5 V	_	_	-100	mA
		high current		3 V	_	—	-60	
V _{OL}	Р	Output	All I/O pins, standard-	5 V, I_{load} = 5 mA	—	—	0.8	V
	С	low voltage	drive strength	3 V, I _{load} = 2.5 mA	—	—	0.8	V
	Р	voltage	High current drive pins,	5 V, I _{load} =20 mA	—	—	0.8	V
	С		high-drive strength ²	3 V, I _{load} = 10 mA	—	—	0.8	V
I _{OLT}	D	Output	Max total I _{OL} for all ports	5 V	_	—	100	mA
		low current		3 V	_	—	60	
V _{IH}	Р	Input	All digital inputs	4.5≤V _{DD} <5.5 V	$0.65 \times V_{DD}$		_	V
		high voltage		2.7≤V _{DD} <4.5 V	$0.70 \times V_{DD}$	—	_	
V _{IL}	Р	Input low voltage	All digital inputs	4.5≤V _{DD} <5.5 V	—	—	0.35 × V _{DD}	V
				2.7≤V _{DD} <4.5 V	_	—	$0.30 \times V_{DD}$	
V _{hys}	С	Input hysteresi s	All digital inputs		$0.06 \times V_{DD}$	—	_	m\
ll _{In} l	Р	Input leakage current	Per pin (pins in high impedance input mode)	$V_{IN} = V_{DD} \text{ or } V_{SS}$	_	0.1	1	μA
{INTOT}	С	Total leakage combine d for all port pins	Pins in high impedance input mode	$V{IN} = V_{DD}$ or V_{SS}	_	_	2	μA
R _{PU}	Р	Pullup resistors	All digital inputs, when enabled (all I/O pins other than PTA2 and PTA3)	_	30.0	_	50.0	kΩ
R _{PU} ³	Р	Pullup resistors	PTA2 and PTA3 pins	—	30.0	-	60.0	kΩ
I _{IC}	D	DC	Single pin limit	$V_{\rm IN} < V_{\rm SS}, V_{\rm IN} >$	-2		2	mA
	injection current ^{4,} 5, 6	Total MCU limit, includes sum of all stressed pins	V _{DD}	-5	-	25		
C _{In}	С	Input	capacitance, all pins	_	_		7	pF
V _{RAM}	С	-	M retention voltage		2.0			V

Table 3.	DC characteristics	(continued)
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Typical values are measured at 25 °C. Characterized, not tested.
 Only PTB4, PTB5, PTD0, PTD1, PTE0, PTE1, PTH0, and PTH1 support high current output.

- 3. The specified resistor value is the actual value internal to the device. The pullup value may appear higher when measured externally on the pin.
- All functional non-supply pins, except for PTA2 and PTA3, are internally clamped to V_{SS} and V_{DD}. PTA2 and PTA3 are true open drain I/O pins that are internally clamped to V_{SS}.
- 5. Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger value.
- 6. Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If the positive injection current (V_{In} > V_{DD}) is higher than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure that external V_{DD} load will shunt current higher than maximum injection current when the MCU is not consuming power, such as when no system clock is present, or clock rate is very low (which would reduce overall power consumption).

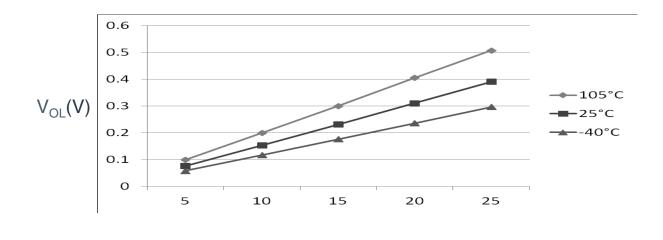
Symbol	С	Desc	ription	Min	Тур	Max	Unit
V _{POR}	D	POR re-a	rm voltage ¹	1.5	1.75	2.0	V
V _{LVDH}	С	threshold-hig	Falling low-voltage detect threshold—high range (LVDV = $1)^2$		4.3	4.4	V
V _{LVW1H}	С	Falling low- voltage	Level 1 falling (LVWV = 00)	4.3	4.4	4.5	V
V _{LVW2H}	С	warning threshold— high range	Level 2 falling (LVWV = 01)	4.5	4.5	4.6	V
V _{LVW3H}	С		Level 3 falling (LVWV = 10)	4.6	4.6	4.7	V
V _{LVW4H}	С		Level 4 falling (LVWV = 11)	4.7	4.7	4.8	V
V _{HYSH}	С		High range low-voltage detect/warning hysteresis		100		mV
V _{LVDL}	С	threshold-lov	Falling low-voltage detect threshold—low range (LVDV = 0)		2.61	2.66	V
V _{LVW1L}	С	Falling low- voltage	Level 1 falling (LVWV = 00)	2.62	2.7	2.78	V
V _{LVW2L}	С	warning threshold— low range	Level 2 falling (LVWV = 01)	2.72	2.8	2.88	V
V _{LVW3L}	С		Level 3 falling (LVWV = 10)	2.82	2.9	2.98	V
V _{LVW4L}	С		Level 4 falling (LVWV = 11)	2.92	3.0	3.08	V
V _{HYSDL}	С		v-voltage detect eresis	—	40	_	mV
V _{HYSWL}	С		low-voltage hysteresis	—	80	_	mV
V _{BG}	Р	Buffered ban	ndgap output ³	1.14	1.16	1.18	V

Table 4. LVD and POR specification

1. Maximum is highest voltage that POR is guaranteed.

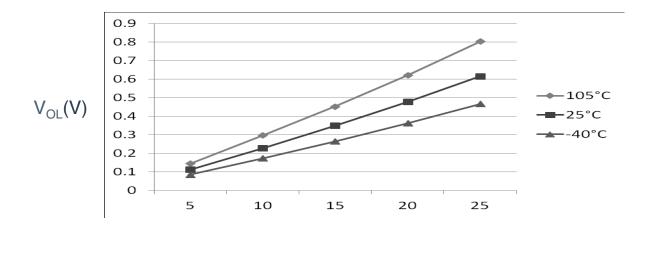
2. Rising thresholds are falling threshold + hysteresis.

3. voltage Factory trimmed at V_{DD} = 5.0 V, Temp = 25 °C



I_{OL}(mA)

Figure 7. Typical V_{OL} Vs. I_{OL} (high drive strength) (V_{DD} = 5 V)



 $I_{OL}(mA) \label{eq:IOL}$ Figure 8. Typical V_{OL} Vs. I_{OL} (high drive strength) (V_{DD} = 3 V)

5.1.2 Supply current characteristics

This section includes information about power supply current in various operating modes.

C	Parameter	Symbol	Core/Bus Freq	V _{DD} (V)	Typical ¹	Max ²	Unit	Temp
С	Run supply current FEI	RI _{DD}	40/20 MHz	5	7.8	_	mA	–40 to 105 °C
С	mode, all modules clocks enabled; run from flash		20/20 MHz		6.7	_		
С	enabled, full norm hash		10/10 MHz		4.5	_		
			1/1 MHz		1.5	_		
С			40/20 MHz	3	7.7	_		
С			20/20 MHz		6.6	_		
С			10/10 MHz		4.4			
			1/1 MHz		1.45			
С	Run supply current FEI	RI _{DD}	40/20 MHz	5	6.3		mA	–40 to 105 °C
С	mode, all modules clocks disabled; run from flash		20/20 MHz		5.3			
С			10/10 MHz		3.7			
			1/1 MHz		1.5			
С			40/20 MHz	3	6.2	—		
С			20/20 MHz		5.3	—		
C			10/10 MHz		3.7	—		
			1/1 MHz		1.4	—		
С	Run supply current FBE	RI _{DD}	40/20 MHz	5	10.3		mA	–40 to 105 °C
Р	mode, all modules clocks enabled; run from RAM		20/20 MHz		9	14.8		
С	,		10/10 MHz		5.2	—		
			1/1 MHz		1.45			
С			40/20 MHz	3	10.2	—		
Р			20/20 MHz		8.8	11.8		
С			10/10 MHz		5.1			
			1/1 MHz		1.4			
С	Run supply current FBE	RI _{DD}	40/20 MHz	5	8.9	—	mA	–40 to 105 °C
Р	mode, all modules clocks disabled; run from RAM		20/20 MHz		8	12.3		
С			10/10 MHz		4.4	—		
			1/1 MHz		1.35	—		
С			40/20 MHz	3	8.8			
Р			20/20 MHz		7.8	9.2		
С			10/10 MHz		4.2			
			1/1 MHz		1.3			

Table 5. Supply current characteristics

Table continues on the next page ...

Peripheral operating requirements and behaviors

Where:

 T_A = Ambient temperature, °C

 θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W

 $P_D = P_{int} + P_{I/O}$

 $P_{int} = I_{DD} \times V_{DD}$, Watts - chip internal power

 $P_{I/O}$ = Power dissipation on input and output pins - user determined

For most applications, $P_{I/O} \ll P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

 $P_{\rm D} = \mathrm{K} \div (\mathrm{T_J} + 273 \ ^{\circ}\mathrm{C})$

Solving the equations above for K gives:

 $\mathbf{K} = \mathbf{P}_{\mathrm{D}} \times (\mathbf{T}_{\mathrm{A}} + 273 \ ^{\circ}\mathrm{C}) + \mathbf{\theta}_{\mathrm{JA}} \times (\mathbf{P}_{\mathrm{D}})^{2}$

where K is a constant pertaining to the particular part. K can be determined by measuring P_D (at equilibrium) for an known T_A . Using this value of K, the values of P_D and T_J can be obtained by solving the above equations iteratively for any value of T_A .

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 SWD electricals

Table 11. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	5.5	V
J1	SWD_CLK frequency of operation			
	Serial wire debug	0	20	MHz
J2	SWD_CLK cycle period	1/J1		ns
J3	SWD_CLK clock pulse width			
	Serial wire debug	20	_	ns
J4	SWD_CLK rise and fall times		3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10		ns
J10	SWD_DIO input data hold time after SWD_CLK rise	3		ns

Table continues on the next page...

Table 12. OSC and ICS specifications (temperature range = -40 to 105 °C ambient)(continued)

Num	С	c	haracteristic	Symbol	Min	Typical ¹	Max	Unit
2	D	Lo	oad capacitors	C1, C2		See Note ²		
3	D	Feedback resistor	Low Frequency, Low-Power Mode ³	R _F		_	_	MΩ
			Low Frequency, High-Gain Mode		—	10	_	MΩ
			High Frequency, Low- Power Mode		—	1	_	MΩ
			High Frequency, High-Gain Mode		—	1	—	MΩ
4	D	Series resistor -	Low-Power Mode ³	R _S	_	0	_	kΩ
		Low Frequency	High-Gain Mode	-	_	200	_	kΩ
5	D	Series resistor - High Frequency	Low-Power Mode ³	R _S	_	0	—	kΩ
	D	Series resistor -	4 MHz		_	0	_	kΩ
	D	High Frequency,	8 MHz	_	_	0	_	kΩ
	D	High-Gain Mode	16 MHz	-	_	0	_	kΩ
6	6 C Crystal start-up		Low range, low power	t _{CSTL}	_	1000		ms
	С	time low range = 32.768 kHz	Low range, high gain	-	_	800		ms
	C crystal; High	High range, low power	t _{CSTH}	_	3	_	ms	
	С	range = 20 MHz crystal ^{4,5}	High range, high gain	-	_	1.5		ms
7	Т	Internal re	eference start-up time	t _{IRST}	_	20	50	μs
8	Р	Internal referenc	e clock (IRC) frequency trim range	f _{int_t}	31.25	_	39.0625	kHz
9	Ρ	Internal reference clock frequency, factory trimmed [,]	T = 25 °C, V _{DD} = 5 V	f _{int_ft}	_	31.25	_	kHz
10	Р	DCO output frequency range	FLL reference = fint_t, flo, or fhi/RDIV	f _{dco}	32	_	40	MHz
11	Р	Factory trimmed internal oscillator accuracy	T = 25 °C, V _{DD} = 5 V	∆f _{int_ft}	-0.5	_	0.5	%
12	С	Deviation of IRC over	Over temperature range from -40 °C to 105°C	Δf_{int_t}	-1	_	0.5	%
		temperature when trimmed at T = 25 °C, $V_{DD} = 5 V$	Over temperature range from 0 °C to 105°C	Δf_{int_t}	-0.5	_	0.5	
13	С	Frequency accuracy of	Over temperature range from -40 °C to 105°C	$\Delta f_{dco_{ft}}$	-1.5	_	1	%
		DCO output using factory trim value	Over temperature range from 0 °C to 105°C	$\Delta f_{dco_{ft}}$	-1	_	1	

Table continues on the next page ...

Table 12. OSC and ICS specifications (temperature range = -40 to 105 °C ambient)(continued)

Num	С	Characteristic	Symbol	Min	Typical ¹	Мах	Unit
14	С	FLL acquisition time ^{4,6}	t _{Acquire}	_	_	2	ms
15	С	Long term jitter of DCO output clock (averaged over 2 ms interval) ⁷	C _{Jitter}		0.02	0.2	%f _{dco}

1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.

- 2. See crystal or resonator manufacturer's recommendation.
- Load capacitors (C₁,C₂), feedback resistor (R_F) and series resistor (R_S) are incorporated internally when RANGE = HGO = 0.
- 4. This parameter is characterized and not tested on each device.
- 5. Proper PC board layout procedures must be followed to achieve specifications.
- This specification applies to any time the FLL reference source or reference divider is changed, trim value changed, or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- 7. Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

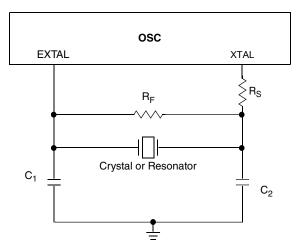


Figure 15. Typical crystal or resonator circuit

6.3 NVM specifications

This section provides details about program/erase times and program/erase endurance for the flash and EEPROM memories.

С	Characteristic	Symbol	Min ¹	Typical ²	Max ³	Unit ⁴
D	Supply voltage for program/erase –40 °C to 105 °C	V _{prog/erase}	2.7		5.5	V
D	Supply voltage for read operation	V _{Read}	2.7	—	5.5	V

Table 13. Flash and EEPROM characteristics

Table continues on the next page...

6.4 Analog

			-		T		1
Characteri stic	Conditions	Symbol	Min	Typ ¹	Max	Unit	Comment
Reference	• Low	V _{REFL}	V _{SSA}	—	V _{SSA}	V	—
potential	• High	V _{REFH}	V_{DDA}	—	V _{DDA}		
Supply	Absolute	V _{DDA}	2.7	—	5.5	V	_
voltage	Delta to V _{DD} (V _{DD} -V _{DDA})	ΔV_{DDA}	-100	0	+100	mV	_
Ground voltage	Delta to V_{SS} (V_{SS} - V_{SSA})	ΔV _{SSA}	-100	0	+100	mV	_
Input voltage		V _{ADIN}	V _{REFL}	_	V _{REFH}	V	_
Input capacitance		C _{ADIN}	—	4.5	5.5	pF	—
Input resistance		R _{ADIN}	_	3	5	kΩ	-
Analog	12-bit mode	R _{AS}	_	_	2	kΩ	External to
source resistance	 f_{ADCK} > 4 MHz f_{ADCK} < 4 MHz 		_		5		MCU
	10-bit mode ● f₄por > 4 MHz		_	_	5		
	 f_{ADCK} > 4 MHz f_{ADCK} < 4 MHz 		_	_	10		
	8-bit mode		_	_	10		
	(all valid f _{ADCK})						
ADC	High speed (ADLPC=0)	f _{ADCK}	0.4	_	8.0	MHz	_
conversion clock frequency	Low power (ADLPC=1)		0.4	_	4.0		

6.4.1 ADC characteristics

Table 14. 5 V 12-bit ADC operating conditions

1. Typical values assume V_{DDA} = 5.0 V, Temp = 25°C, f_{ADCK}=1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

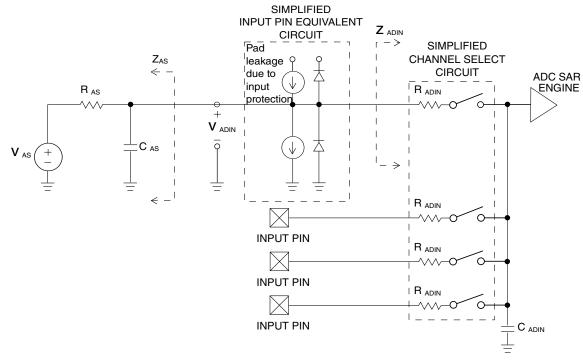


Figure 16. ADC input impedance equivalency diagram

Table 15. 12-bit ADC characteristics	$(V_{REFH} = V_{DDA})$, V _{REFL} = V _{SSA})
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Characteristic	Conditions	С	Symbol	Min	Typ ¹	Мах	Unit
Supply current		Т	I _{DDA}	_	133	—	μA
ADLPC = 1							
ADLSMP = 1							
ADCO = 1							
Supply current		Т	I _{DDA}	_	218		μA
ADLPC = 1							
ADLSMP = 0							
ADCO = 1							
Supply current		Т	I _{DDA}	—	327	_	μA
ADLPC = 0							
ADLSMP = 1							
ADCO = 1							
Supply current		Т	I _{DDA}		582	990	μA
ADLPC = 0							
ADLSMP = 0							
ADCO = 1							
Supply current	Stop, reset, module off	Т	I _{DDA}		0.011	1	μA
ADC asynchronous clock source	High speed (ADLPC = 0)	Р	f _{ADACK}	2	3.3	5	MHz

Table continues on the next page ...

6.4.2 Analog comparator (ACMP) electricals Table 16. Comparator electrical specifications

С	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DDA}	2.7	—	5.5	V
Т	Supply current (Operation mode)	I _{DDA}	—	10	20	μA
D	Analog input voltage	V _{AIN}	V _{SS} - 0.3		V _{DDA}	V
Р	Analog input offset voltage	V _{AIO}	—	—	40	mV
С	Analog comparator hysteresis (HYST=0)	V _H	—	15	20	mV
С	Analog comparator hysteresis (HYST=1)	V _H		20	30	mV
Т	Supply current (Off mode)	IDDAOFF	—	60	—	nA
С	Propagation Delay	t _D		0.4	1	μs

6.5 Communication interfaces

6.5.1 SPI switching specifications

The serial peripheral interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's reference manual for information about the modified transfer formats used for communicating with slower peripheral devices. All timing is shown with respect to 20% V_{DD} and 80% V_{DD} , unless noted, and 25 pF load on all SPI pins. All timing assumes high-drive strength is enabled for SPI output pins.

Nu m.	Symbol	Description	Min.	Max.	Unit	Comment
1	f _{op}	Frequency of operation	f _{Bus} /2048	f _{Bus} /2	Hz	f _{Bus} is the bus clock
2	t _{SPSCK}	SPSCK period	2 x t _{Bus}	2048 x t _{Bus}	ns	$t_{Bus} = 1/f_{Bus}$
3	t _{Lead}	Enable lead time	1/2	—	t _{SPSCK}	
4	t _{Lag}	Enable lag time	1/2	—	t _{SPSCK}	
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{Bus} – 30	1024 x t _{Bus}	ns	
6	t _{SU}	Data setup time (inputs)	8	—	ns	
7	t _{HI}	Data hold time (inputs)	8	—	ns	
8	t _v	Data valid (after SPSCK edge)	—	25	ns	—
9	t _{HO}	Data hold time (outputs)	20	—	ns	—
10	t _{RI}	Rise time input	—	t _{Bus} – 25	ns	—

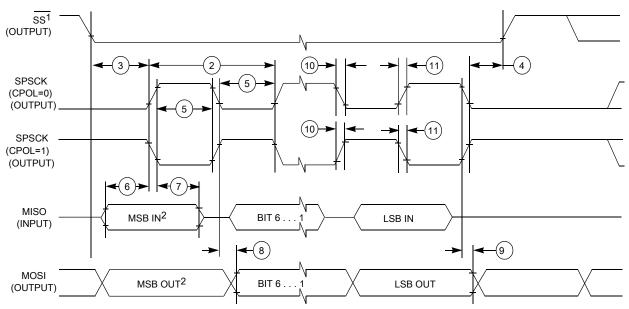
Table 17. SPI master mode timing

Table continues on the next page...

Peripheral operating requirements and behaviors

Nu m.	Symbol	Description	Min.	Max.	Unit	Comment
	t _{FI}	Fall time input				
11	t _{RO}	Rise time output	—	25	ns	—
	t _{FO}	Fall time output				

Table 17. SPI master mode timing (continued)



1. If configured as an output.

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

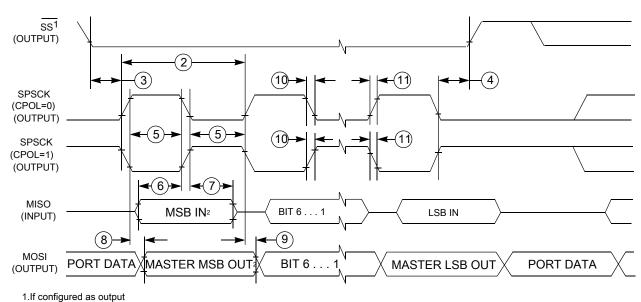


Figure 17. SPI master mode timing (CPHA=0)

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 18. SPI master mode timing (CPHA=1)

Peripheral operating requirements and behaviors

Nu m.	Symbol	Description	Min.	Max.	Unit	Comment
1	f _{op}	Frequency of operation	0	f _{Bus} /4	Hz	f _{Bus} is the bus clock as defined in Control timing.
2	t _{SPSCK}	SPSCK period	4 x t _{Bus}	—	ns	$t_{Bus} = 1/f_{Bus}$
3	t _{Lead}	Enable lead time	1	—	t _{Bus}	-
4	t _{Lag}	Enable lag time	1	—	t _{Bus}	-
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{Bus} - 30	—	ns	-
6	t _{SU}	Data setup time (inputs)	15	—	ns	-
7	t _{HI}	Data hold time (inputs)	25	—	ns	-
8	t _a	Slave access time	—	t _{Bus}	ns	Time to data active from high-impedance state
9	t _{dis}	Slave MISO disable time	-	t _{Bus}	ns	Hold time to high- impedance state
10	t _v	Data valid (after SPSCK edge)		25	ns	—
11	t _{HO}	Data hold time (outputs)	0	—	ns	—
12	t _{RI}	Rise time input		t _{Bus} - 25	ns	—
	t _{FI}	Fall time input				
13	t _{RO}	Rise time output	_	25	ns	-
	t _{FO}	Fall time output				



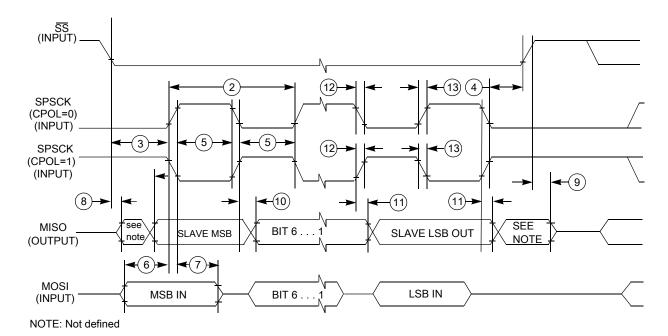


Figure 19. SPI slave mode timing (CPHA = 0)

8 Pinout

8.1 Signal multiplexing and pin assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

Pin Number			Lowest Priority <> Highest						
64-QFP/ LQFP	44-LQFP	32- LQFP/QFN	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4		
1	1	1	PTD1 ¹	KBI1_P1	FTM2_CH3	SPI1_MOSI	—		
2	2	2	PTD0 ¹	KBI1_P0	FTM2_CH2	SPI1_SCK	—		
3			PTH7	—	—	—	—		
4			PTH6	—	—	—	_		
5	3	—	PTE7	—	FTM2_CLK	—	FTM1_CH1		
6	4	_	PTH2	—	BUSOUT	—	FTM1_CH0		
7	5	3	—	—	—	—	VDD		
8	6	4	—	—	—	VDDA	VREFH ²		
9	7	5	—	—	—	—	VREFL		
10	8	6	—	—	—	VSSA	VSS ³		
11	9	7	PTB7	—	I2C0_SCL	—	EXTAL		
12	10	8	PTB6	—	I2C0_SDA	—	XTAL		
13	11	_	—	—	—	—	VSS		
14	—	—	PTH1 ¹	_	FTM2_CH1	—	—		
15	—	—	PTH0 ¹	_	FTM2_CH0	—	—		
16	_	—	PTE6	_	—	—	—		
17	—	—	PTE5	_	—	—	—		
18	12	9	PTB5 ¹	FTM2_CH5	SPI0_PCS0	ACMP1_OUT	—		
19	13	10	PTB4 ¹	FTM2_CH4	SPI0_MISO	NMI	ACMP1_IN2		
20	14	11	PTC3	FTM2_CH3	—	—	ADC0_SE11		
21	15	12	PTC2	FTM2_CH2	—	—	ADC0_SE10		
22	16		PTD7	KBI1_P7	UART2_TX	—	—		
23	17	—	PTD6	KBI1_P6	UART2_RX	—	—		
24	18		PTD5	KBI1_P5	_	—	—		
25	19	13	PTC1	-	FTM2_CH1	—	ADC0_SE9		
26	20	14	PTC0	—	FTM2_CH0	—	ADC0_SE8		
27	_	—	PTF7	—	—	—	ADC0_SE15		

Table 19. Pin availability by package pin-count

Table continues on the next page...

Table 19.	Pin availability b	/ package pi	n-count (continued)
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Pin Number			Lowest Priority <> Highest						
64-QFP/ LQFP	44-LQFP	32- LQFP/QFN	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4		
28		_	PTF6		_		ADC0_SE14		
29			PTF5		_		ADC0_SE13		
30	_	_	PTF4		_		ADC0_SE12		
31	21	15	PTB3	KBI0_P7	SPI0_MOSI	FTM0_CH1	ADC0_SE7		
32	22	16	PTB2	KBI0_P6	SPI0_SCK	FTM0_CH0	ADC0_SE6		
33	23	17	PTB1	KBI0_P5	UART0_TX	_	ADC0_SE5		
34	24	18	PTB0	KBI0_P4	UART0_RX	_	ADC0_SE4		
35		_	PTF3	_			_		
36		_	PTF2		_		_		
37	25	19	PTA7		FTM2_FLT2	ACMP1_IN1	ADC0_SE3		
38	26	20	PTA6		FTM2_FLT1	ACMP1_IN0	ADC0_SE2		
39		_	PTE4				_		
40	27	_					VSS		
41	28	_	_				VDD		
42		_	PTF1						
43			PTF0				_		
44	29	_	PTD4	KBI1_P4			_		
45	30	21	PTD3	KBI1_P3	SPI1_PCS0		_		
46	31	22	PTD2	KBI1_P2	SPI1_MISO		_		
47	32	23	PTA3 ⁴	KBI0_P3	UART0_TX	I2C0_SCL	_		
48	33	24	PTA2 ⁴	 KBI0_P2	UART0_RX	I2C0_SDA	_		
49	34	25	PTA1	 KBI0_P1	FTM0_CH1	ACMP0_IN1	ADC0_SE1		
50	35	26	PTA0	 KBI0_P0	FTM0_CH0	ACMP0_IN0	ADC0_SE0		
51	36	27	PTC7		UART1_TX		_		
52	37	28	PTC6		UART1_RX		_		
53		_	PTE3		SPI0_PCS0		_		
54	38	_	PTE2		SPI0_MISO		_		
55			PTG3						
56			PTG2						
57			PTG1				_		
58			PTG0						
59	39	_	PTE1 ¹		SPI0_MOSI	_			
60	40	_	PTE0 ¹		SPI0_SCK	FTM1_CLK			
61	40	29	PTC5		FTM1_CH1		RTCO		
62	41	30	PTC4	RTCO	FTM1_CH1	ACMP0_IN2	SWD_CLK		
63	42	30	PTA5	IRQ	FTM1_CH0		RESET		
64	43	32	PTA5 PTA4		ACMP0_OUT		SWD_DIO		

1. This is a high-current drive pin when operated as output.

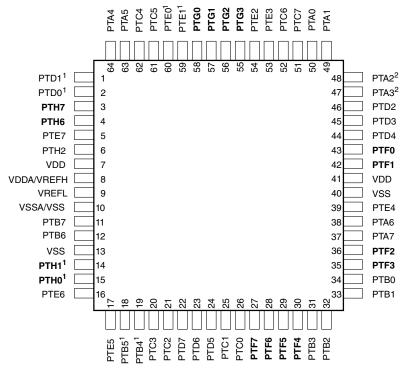
Pinout

- 2. VREFH and VDDA are internally connected.
- 3. VSSA and VSS are internally connected.
- 4. This is a true open-drain pin when operated as output.

Note

When an alternative function is first enabled, it is possible to get a spurious edge to the module. User software must clear any associated flags before interrupts are enabled. Table 19 illustrates the priority if multiple modules are enabled. The highest priority module will have control over the pin. Selecting a higher priority pin function with a lower priority function already enabled can cause spurious edges to the lower priority module. Disable all modules that share a pin before enabling another module.

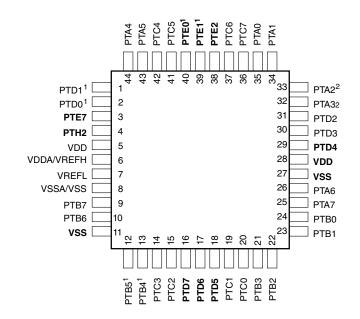
8.2 Device pin assignment



Pins in **bold** are not available on less pin-count packages. 1. High source/sink current pins

2. True open drain pins





Pins in **bold** are not available on less pin-count packages. 1. High source/sink current pins

High source/sink curren
 True open drain pins

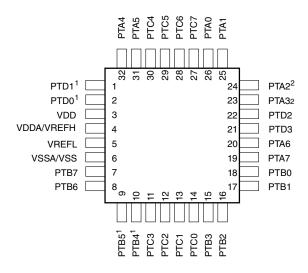
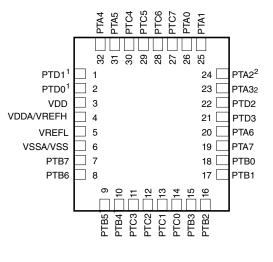


Figure 22. 44-pin LQFP package

1. High source/sink current pins 2. True open drain pins

Figure 23. 32-pin LQFP package



1. High source/sink current pins

2. True open drain pins

Figure 24. 32-pin QFN package

9 Revision history

The following table provides a revision history for this document.

Rev. No.	Date	Substantial Changes
2	3/2014	Initial public release.
3	10/2014	 Added new package of 32-pin QFN information Updated pin-out Updated key features of UART, KBI and ADC in the front page Added a note to the Max. in Supply current characteristics Updated footnote f_{OSC} = 10 MHz (crystal) in EMC radiated emissions operating behaviors Added a new section of Thermal operating requirements Updated NVM specifications Added reference potential in ADC characteristics Updated to "All timing assumes high-drive strength is enabled for SPI output pins." in SPI switching specifications
4	07/2016	• Updated the Typical value of E_{TUE} in 12-bit mode and added a note to the 12-bit mode of E_{TUE} and INL in the ADC characteristics.

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